

Provisional Data

Medium Voltage Thyristor Types P0349LC600 to P0349LC650

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{DRM}	Repetitive peak off-state voltage, (note 1)	6000-6500	V
V_{DSM}	Non-repetitive peak off-state voltage, (note 1)	6000-6500	V
V_{RRM}	Repetitive peak reverse voltage, (note 1)	6000-6500	V
V_{RSM}	Non-repetitive peak reverse voltage, (note 1)	6100-6600	V

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
$I_{T(AV)}$	Mean on-state current. $T_{sink}=55^{\circ}C$, (note 2)	349	A
$I_{T(AV)}$	Mean on-state current. $T_{sink}=85^{\circ}C$, (note 2)	221	A
$I_{T(AV)}$	Mean on-state current. $T_{sink}=85^{\circ}C$, (note 3)	134	A
$I_{T(RMS)}$	Nominal RMS on-state current. $T_{sink}=25^{\circ}C$, (note 2)	705	A
$I_{T(D.C.)}$	D.C. on-state current. $T_{sink}=25^{\circ}C$, (note 4)	622	A
I_{TSM}	Peak non-repetitive surge $t_p=10ms$, $V_{RM}=0.6V_{RRM}$, (note 5)	4800	kA
I_{TSM2}	Peak non-repetitive surge $t_p=10ms$, $V_{RM}\leq 10V$, (note 5)	5300	kA
I^2t	I^2t capacity for fusing $t_p=10ms$, $V_{RM}=0.6V_{RRM}$, (note 5)	115×10^3	A^2s
I^2t	I^2t capacity for fusing $t_p=10ms$, $V_{RM}\leq 10V$, (note 5)	140×10^3	A^2s
di_T/dt	Maximum rate of rise of on-state current (repetitive), (Note 6)	150	$A/\mu s$
	Maximum rate of rise of on-state current (non-repetitive), (Note 6)	300	$A/\mu s$
V_{RGM}	Peak reverse gate voltage	5	V
$P_{G(AV)}$	Mean forward gate power	2	W
P_{GM}	Peak forward gate power	30	W
V_{GD}	Non-trigger gate voltage, (Note 7)	0.25	V
T_{HS}	Operating temperature range	-40 to +125	$^{\circ}C$
T_{stg}	Storage temperature range	-40 to +150	$^{\circ}C$

Notes:-

- 1) De-rating factor of 0.13% per $^{\circ}C$ is applicable for T_j below $25^{\circ}C$.
- 2) Double side cooled, single phase; 50Hz, 180° half-sinewave.
- 3) Single side cooled, single phase; 50Hz, 180° half-sinewave.
- 4) Double side cooled.
- 5) Half-sinewave, $115^{\circ}C$ T_j initial.
- 6) $V_D=67\% V_{DRM}$, $I_{TM}=1000A$, $I_{FG}=2A$, $t_r\leq 0.5\mu s$, $T_{case}=115^{\circ}C$.
- 7) Rated V_{DRM} .

Characteristics

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS
V_{TM}	Maximum peak on-state voltage	-	-	2.8	$I_{TM}=500A$	V
V_0	Threshold voltage	-	-	1.568		V
r_s	Slope resistance	-	-	2.428		mΩ
dv/dt	Critical rate of rise of off-state voltage	1000	-	-	$V_D=80\% V_{DRM}$, linear ramp	V/μs
I_{DRM}	Peak off-state current	-	-	50	Rated V_{DRM}	mA
I_{RRM}	Peak reverse current	-	-	50	Rated V_{RRM}	mA
V_{GT}	Gate trigger voltage	-	-	3.0	$T_J=25^\circ C$, $V_D=10V$, $I_T=2A$	V
I_{GT}	Gate trigger current	-	-	300		mA
I_H	Holding current	-	-	1000	$T_J=25^\circ C$	mA
t_{gd}	Gate controlled turn-on delay time	-	0.6	1.2	$I_{FG}=2A$, $t_r=0.5\mu s$, $V_D=67\%V_{DRM}$, $I_{TM}=1000A$, $di/dt=10A/\mu s$, $T_J=25^\circ C$	μs
t_{gt}	Turn-on time	-	6.0	9.0		
Q_{rr}	Recovered Charge	-	1700	-		μC
Q_{ra}	Recovered Charge, 50% chord	-	900	1075	$I_{TM}=1000A$, $t_p=1ms$, $di/dt=10A/\mu s$, $V_r=50V$	μC
I_{rm}	Reverse recovery current	-	90	-		A
t_{rr}	Reverse recovery time, 50% chord	-	24	-		μs
t_q	Turn-off time	-	800	900	$I_{TM}=1000A$, $t_p=1ms$, $di/dt=10A/\mu s$, $V_r=50V$, $V_{dr}=33\%V_{DRM}$, $dV_{dr}/dt=20V/\mu s$	μs
		-	1080	1200	$I_{TM}=1000A$, $t_p=1ms$, $di/dt=10A/\mu s$, $V_r=50V$, $V_{dr}=33\%V_{DRM}$, $dV_{dr}/dt=200V/\mu s$	
$R_{th(j-hs)}$	Thermal resistance, junction to heatsink	-	-	0.047	Double side cooled	K/W
		-	-	0.094	Single side cooled	K/W
F	Mounting force	10	-	20		kN
W_t	Weight	-	340	-		g

Notes: -

1) Unless otherwise indicated $T_J=115^\circ C$.**Introduction**

The P0349LC series of Medium Voltage Thyristors consists of a fully floating silicon slice (manufacturing reference PAZ) with a partially distributed, regenerative gate mounted in a cold welded capsule.

Notes on Ratings and Characteristics

1.0 Voltage Grade Table

Voltage Grade	V_{DRM} V	V_{DSM} V	V_{RRM} V	V_{RSM} V	V_D / V_R DC V
60		6000		6100	3000
62		6200		6300	3100
64		6400		6500	3200
65		6500		6600	3250

2.0 Extension of Voltage Grades

This report is applicable to other voltage grades when supply has been agreed by Sales/Production.

3.0 De-rating Factor

A blocking voltage de-rating factor of 0.13%/°C is applicable to this device for T_j below 25°C.

4.0 Repetitive dv/dt

Standard dv/dt is 1000V/μs.

5.0 Computer Modelling Parameters

5.1 Device Dissipation Calculations

$$I_{AV} = \frac{-V_0 + \sqrt{V_0^2 + 4 \cdot ff^2 \cdot r_s \cdot W_{AV}}}{2 \cdot ff^2 \cdot r_s} \quad \text{and:} \quad W_{AV} = \frac{\Delta T}{R_{th}}$$

$$\Delta T = T_{j\max} - T_{Hs}$$

Where $V_0=1.568V$, $r_s=2.428m\Omega$,

R_{th} = Supplementary thermal impedance, see table below.

ff = Form factor, see table below.

Supplementary Thermal Impedance							
Conduction Angle	30°	60°	90°	120°	180°	270°	d.c.
Square wave Double Side Cooled	0.0509	0.0504	0.0499	0.0494	0.0485	0.0474	0.047
Square wave Single Side Cooled	0.0987	0.0981	0.0976	0.0972	0.0963	0.0952	0.094
Sine wave Double Side Cooled	0.0505	0.0498	0.0493	0.0489	0.0475		
Sine wave Single Side Cooled	0.0983	0.0976	0.0971	0.0966	0.0953		

Form Factors							
Conduction Angle	30°	60°	90°	120°	180°	270°	d.c.
Square wave	3.464	2.449	2	1.732	1.414	1.149	1
Sine wave	3.98	2.778	2.22	1.879	1.57		

5.2 Calculating V_T using ABCD Coefficients

The on-state characteristic I_T vs. V_T , on page 5 is represented in two ways;

- (i) the well established V_0 and r_s tangent used for rating purposes and
- (ii) a set of constants A, B, C, D, forming the coefficients of the representative equation for V_T in terms of I_T given below:

$$V_T = A + B \cdot \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

The constants, derived by curve fitting software, are given below for both hot and cold characteristics. The resulting values for V_T agree with the true device characteristic over a current range, which is limited to that plotted.

25°C Coefficients		125°C Coefficients	
A	0.2103143	A	-0.8731799
B	0.4754865	B	0.650089
C	2.581886×10^{-3}	C	3.072624×10^{-3}
D	-0.09062255	D	-0.08511282

5.3 D.C. Thermal Impedance Calculation

$$r_t = \sum_{p=1}^{p=n} r_p \cdot \left(1 - e^{-\frac{t}{\tau_p}} \right)$$

Where $p = 1$ to n , n is the number of terms in the series and:

t = Duration of heating pulse in seconds.

r_t = Thermal resistance at time t .

r_p = Amplitude of p_{th} term.

τ_p = Time Constant of r_{th} term.

D.C. Double Side Cooled				
Term	1	2	3	4
r_p	0.02328162	0.0165603	4.739431×10^{-3}	1.805256×10^{-3}
τ_p	0.7294482	0.1571701	0.0343812	0.01059348

D.C. Single Side Cooled				
Term	1	2	3	4
r_p	0.06051172	0.0215729	9.551987×10^{-3}	2.562011×10^{-3}
τ_p	5.722131	0.3167688	0.06285918	0.01198397

Curves

Figure 1 – On-state characteristics of Limit device

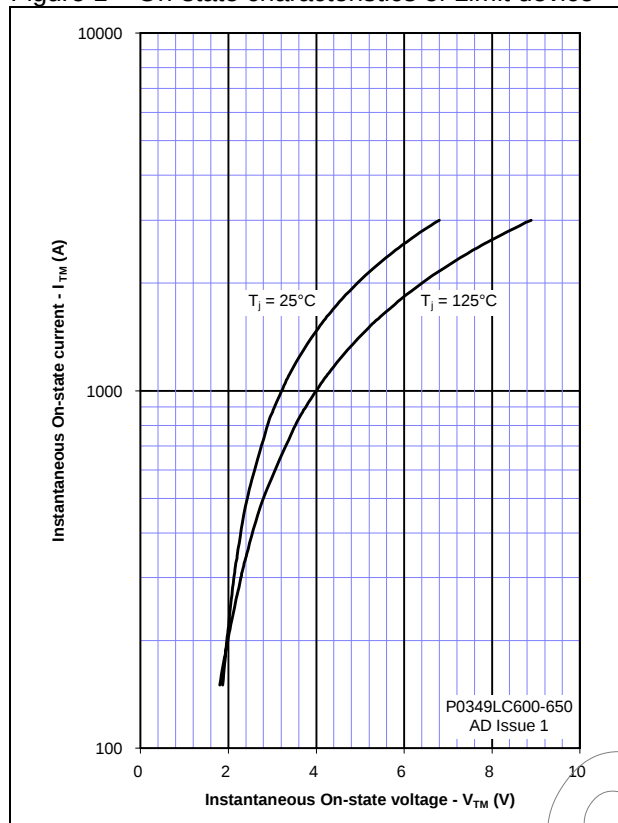


Figure 2 - Transient Thermal Impedance

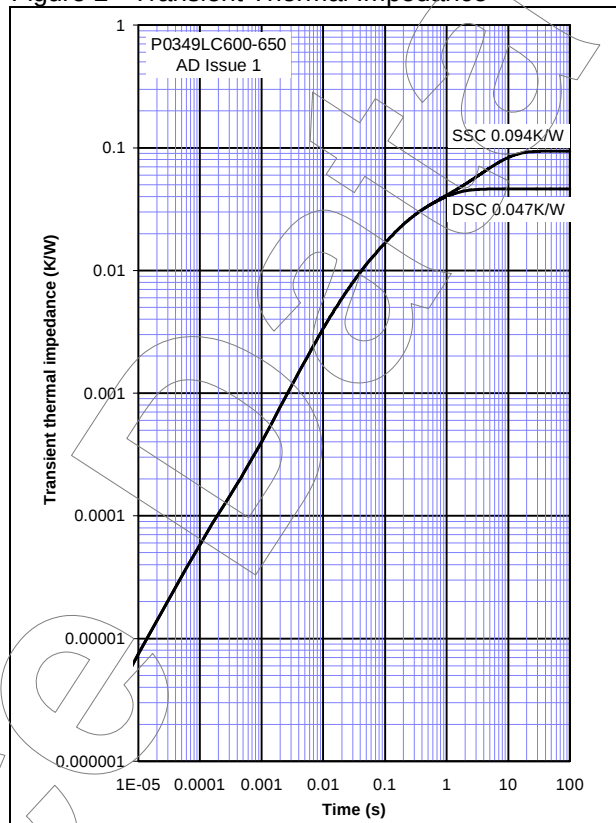


Figure 3 – Gate Characteristics - Trigger Limits

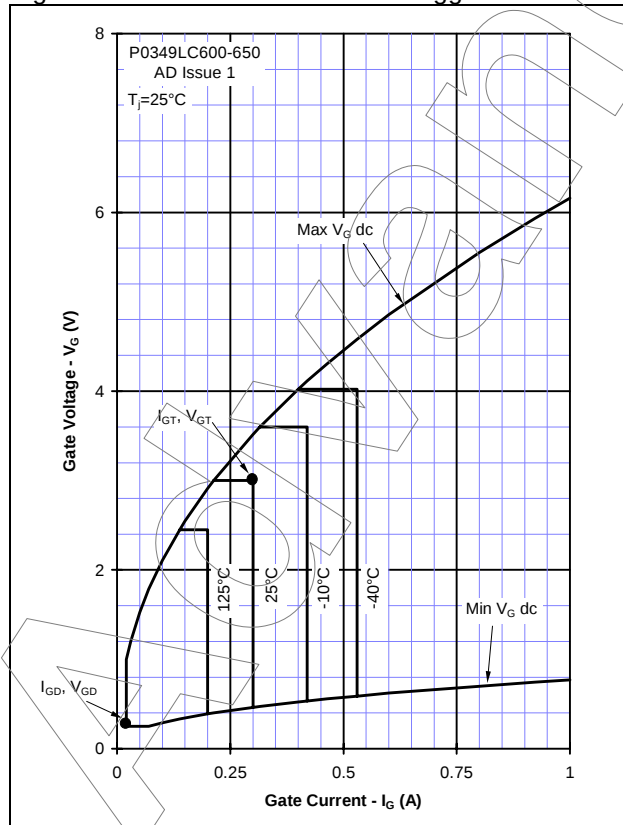


Figure 4 - Gate Characteristics - Power Curves

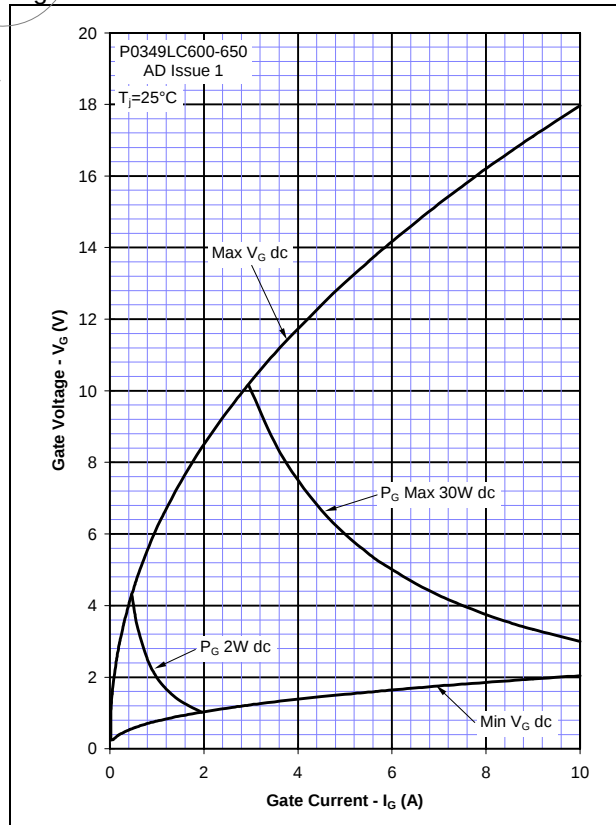


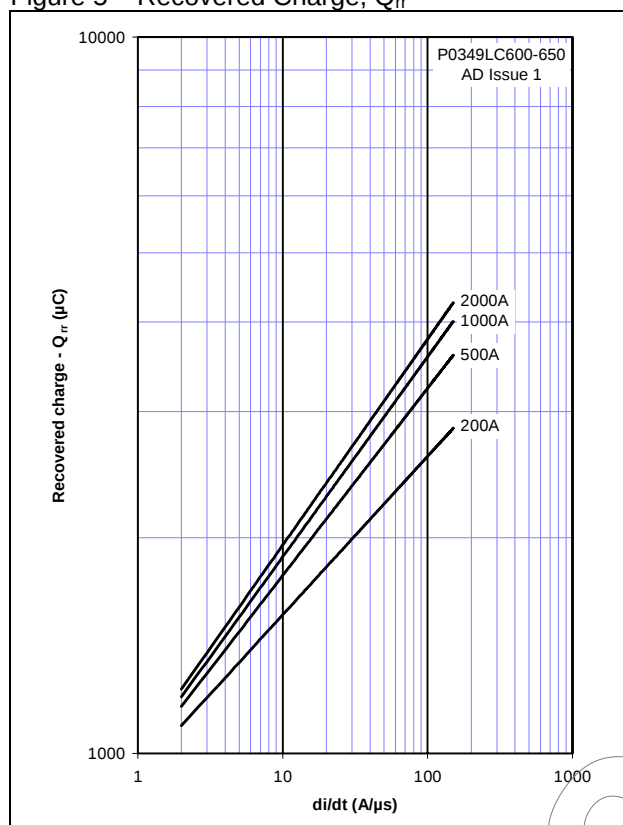
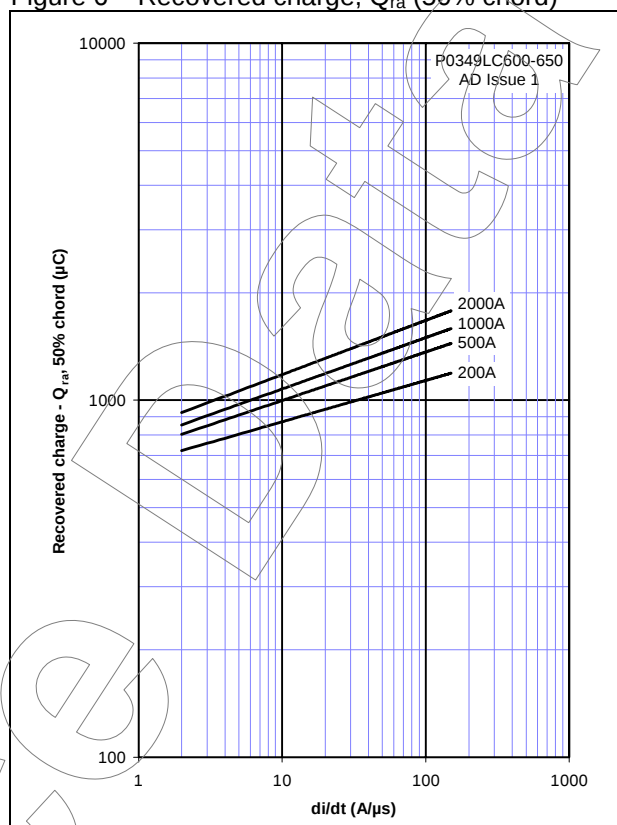
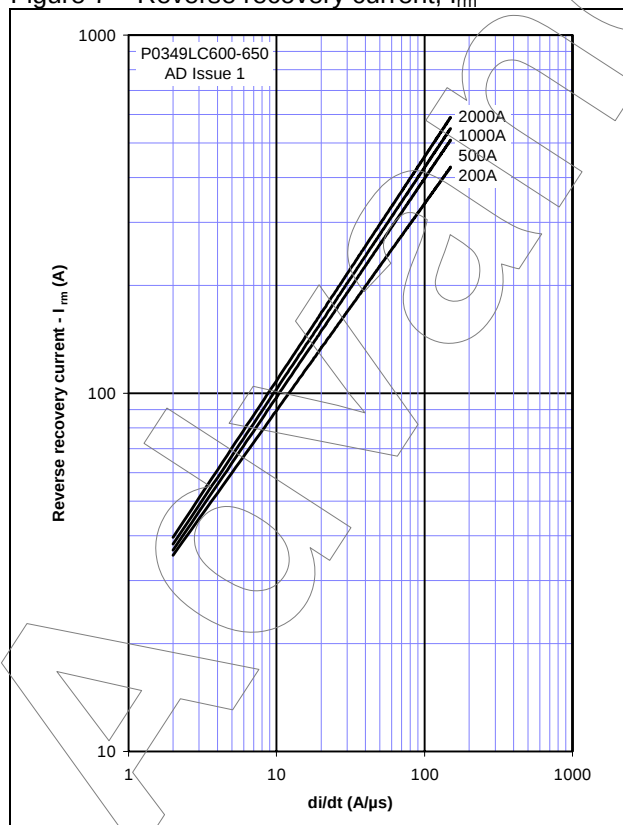
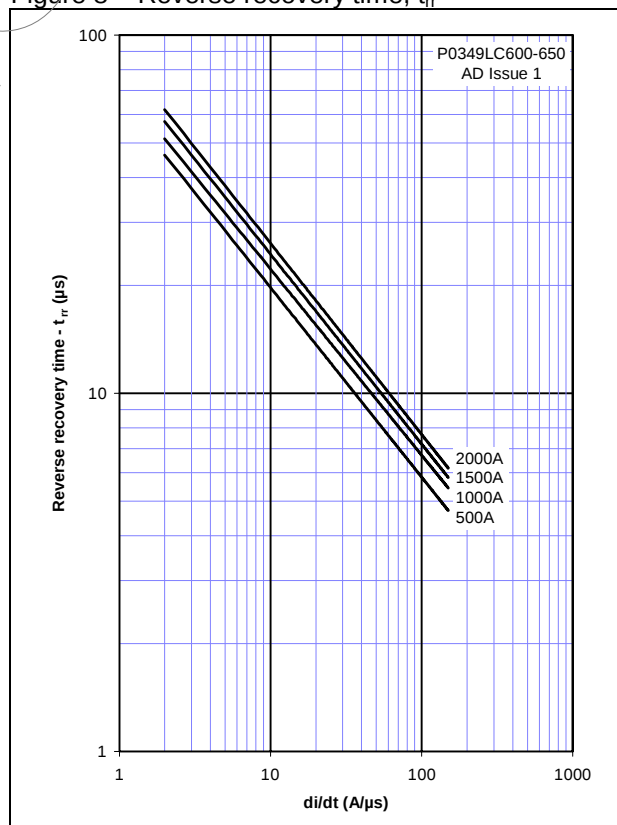
Figure 5 – Recovered Charge, Q_{rr} Figure 6 – Recovered charge, Q_{ra} (50% chord)Figure 7 – Reverse recovery current, I_{rm} Figure 8 – Reverse recovery time, t_{rr} 

Figure 9 – On-state current vs. Power dissipation – Double Side Cooled (Sine wave)

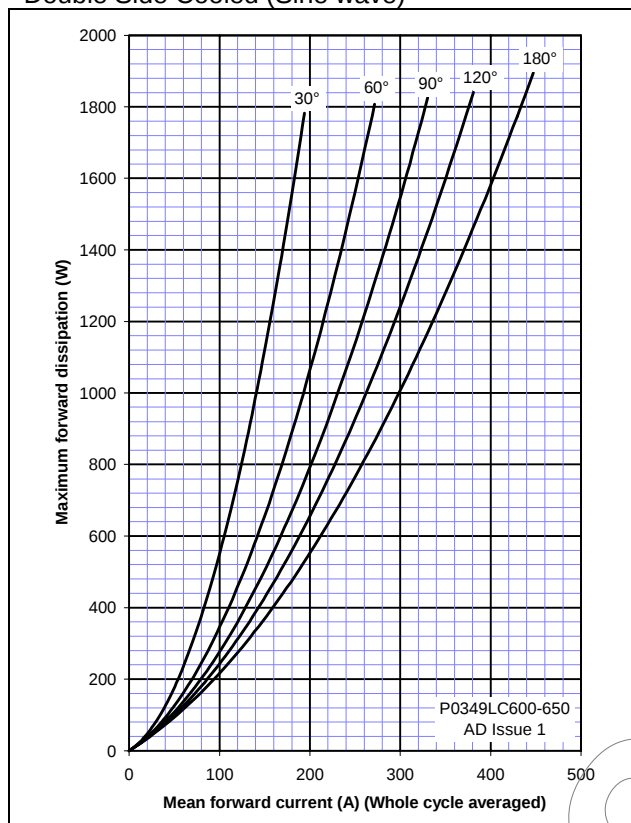


Figure 10 – On-state current vs. Heatsink temperature - Double Side Cooled (Sine wave)

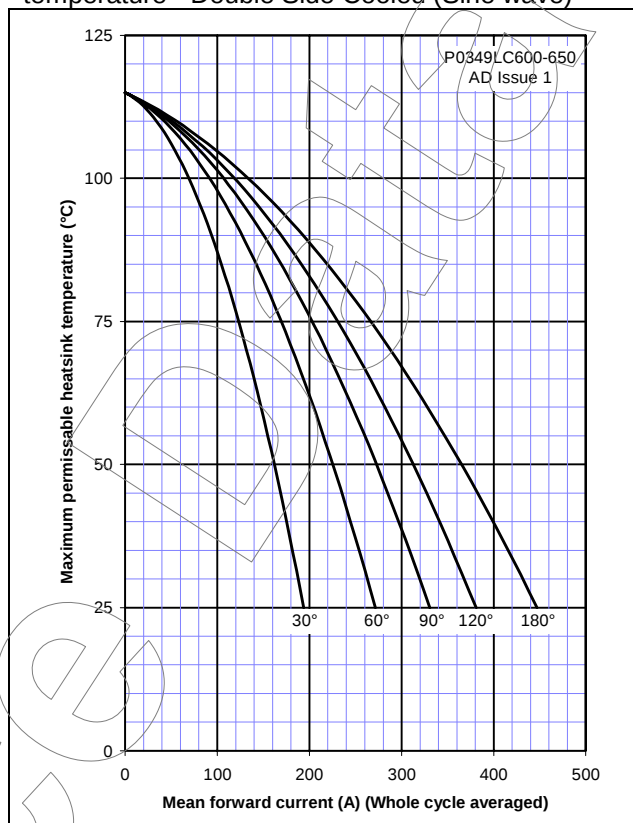


Figure 11 – On-state current vs. Power dissipation – Double Side Cooled (Square wave)

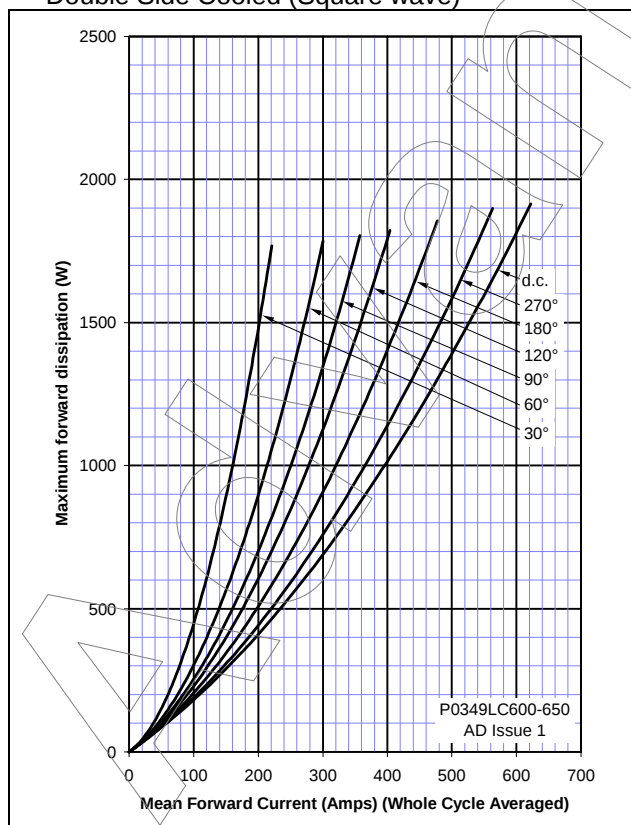


Figure 12 – On-state current vs. Heatsink temperature – Double Side Cooled (Square wave)

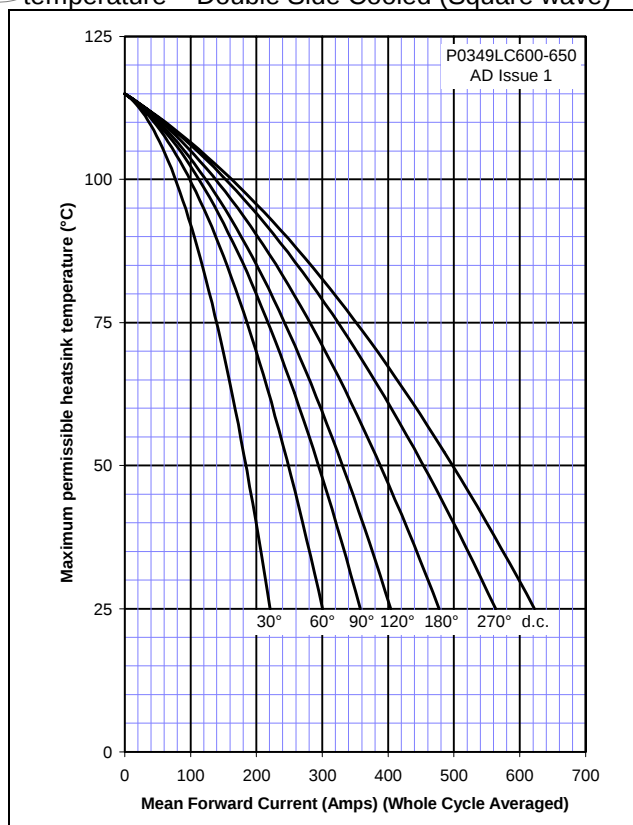


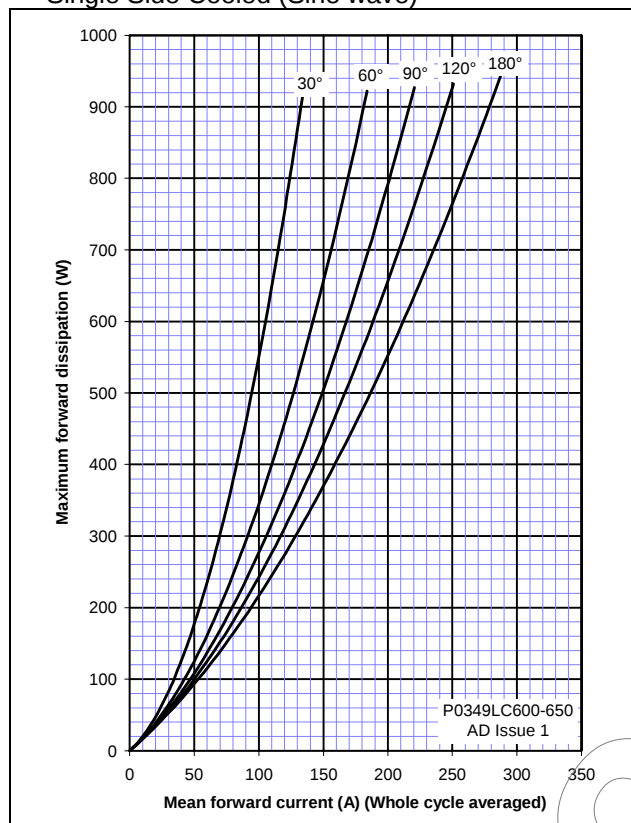
Figure 13 – On-state current vs. Power dissipation
– Single Side Cooled (Sine wave)

Figure 14 – On-state current vs. Heatsink temperature – Single Side Cooled (Sine wave)

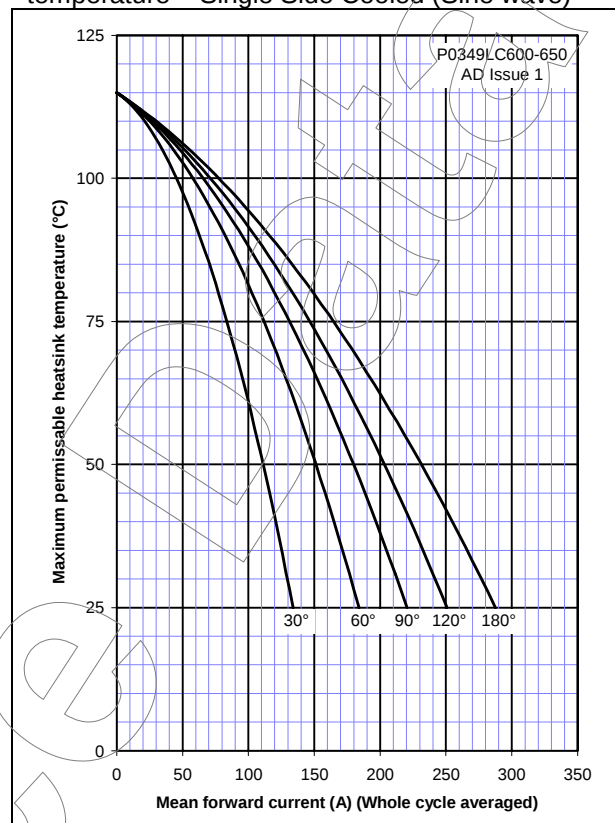
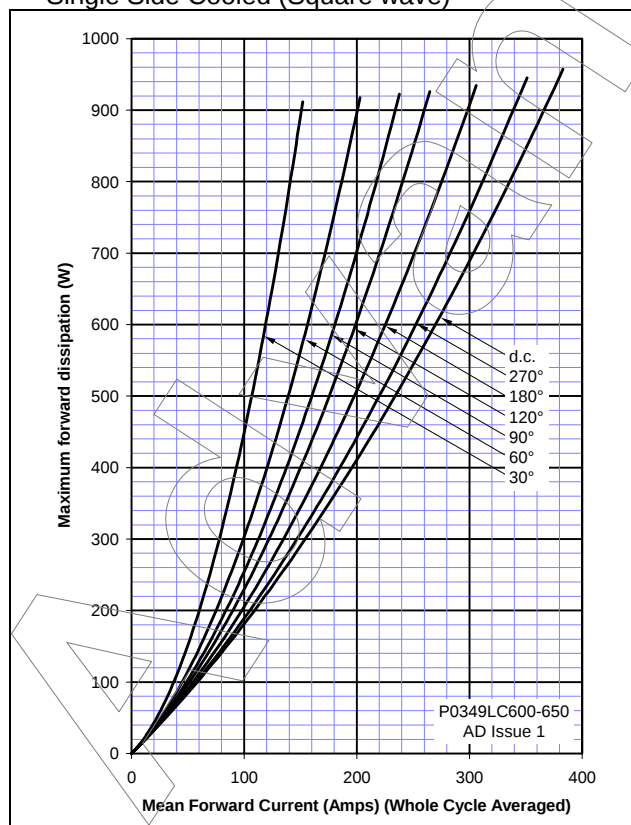
Figure 15 – On-state current vs. Power dissipation
– Single Side Cooled (Square wave)

Figure 16 – On-state current vs. Heatsink temperature – Single Side Cooled (Square wave)

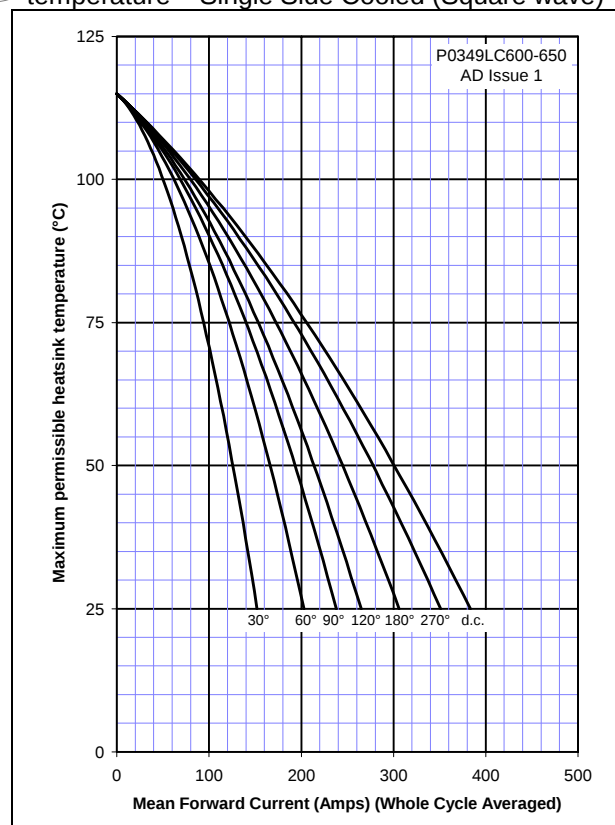
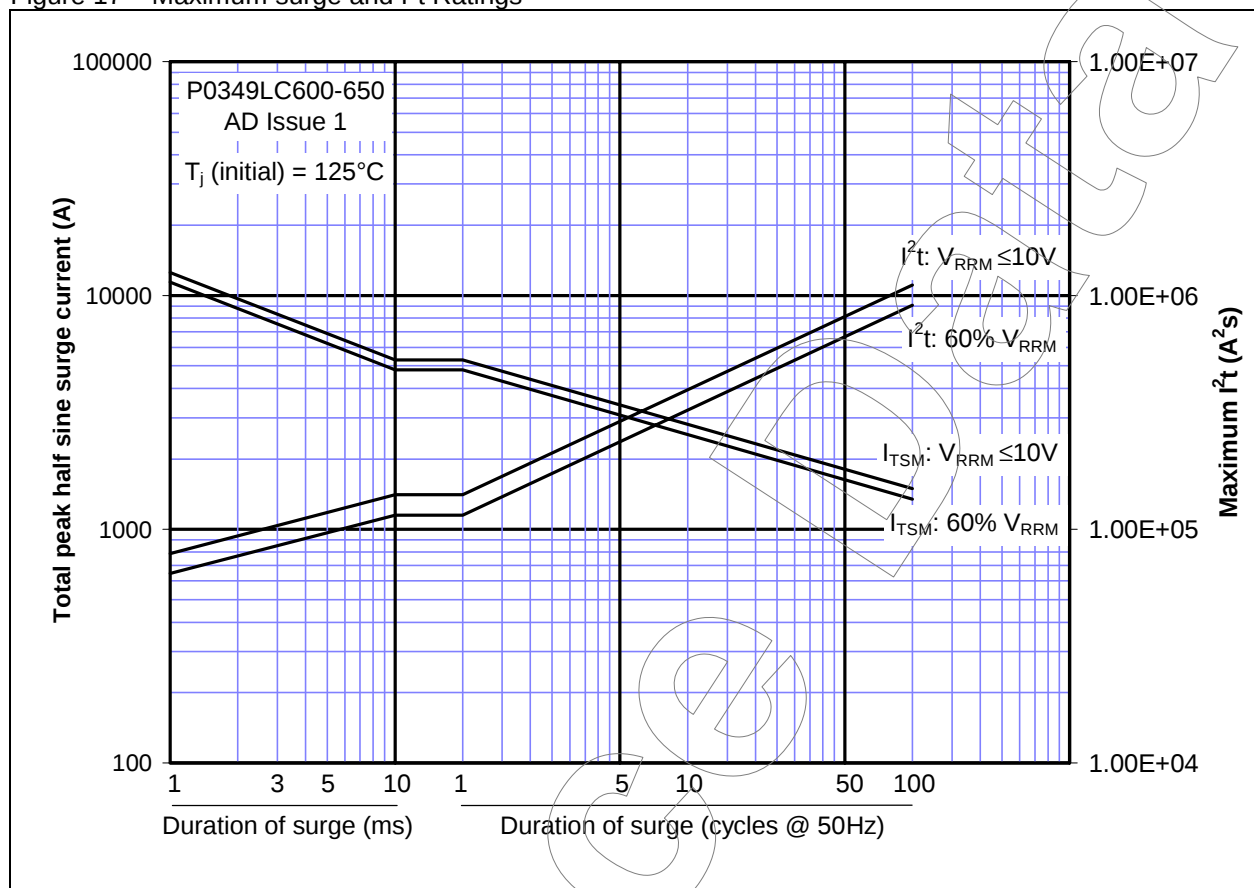


Figure 17 – Maximum surge and I^2t Ratings

Outline Drawing & Ordering Information